Quad 2:1 Multiplexer/ Demultiplexer Bus Switch

The ON Semiconductor 74FST3257 is a quad 2:1, high performance multiplexer/demultiplexer bus switch. The device is CMOS TTL compatible when operating between 4 and 5.5 Volts. The device exhibits extremely low R_{ON} and adds nearly zero propagation delay. The device adds no noise or ground bounce to the system.

Features

- $R_{ON} < 4 \Omega$ Typical
- Less Than 0.25 ns-Max Delay Through Switch
- Nearly Zero Standby Current
- No Circuit Bounce
- Control Inputs are TTL/CMOS Compatible
- Pin-For-Pin Compatible With QS3257, FST3257, CBT3257
- All Popular Packages: SOIC-16, TSSOP-16, QFN16
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

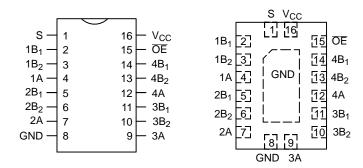


Figure 1. 16-Lead Pinout Diagrams

S	ŌĒ	Function
Х	Н	Disconnect
L	L	A = B ₁
Н	L	A = B ₂

Figure 2. Truth Table



ON Semiconductor®

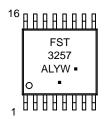
www.onsemi.com





MARKING DIAGRAMS









A = Assembly Location
WL, L = Wafer Lot
Y = Year
WW, W = Work Week
G or = Pb-Free Package
(Note: Microdot may be in either location)

PIN NAMES

Pin	Description
\overline{OE}_1 , \overline{OE}_2	Bus Switch Enables
S ₀ , S ₁	Select Inputs
А	Bus A
B ₁ , B ₂ , B ₃ , B ₄	Bus B

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

1

74FST3257

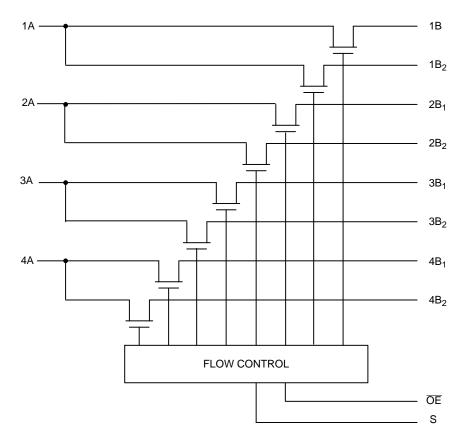


Figure 3. Logic Diagram

ORDERING INFORMATION

Device Order Number	Package	Shipping [†]
74FST3257DR2G	SOIC-16	OF OO Heite / Tame 9 Deal
NLV74FST3257DR2G*	(Pb-Free)	2500 Units / Tape & Reel
74FST3257DTR2G	TSSOP-16 (Pb-Free)	2500 Units / Tape & Reel
74FST3257MNTWG	QFN16 (Pb-Free)	3000 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

Capable.

74FST3257

MAXIMUM RATINGS

Symbol	Parameter	Value	Units
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
VI	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage	-0.5 to +7.0	V
I _{IK}	DC Input Diode Current V _I < GND	-50	mA
I _{OK}	DC Output Diode Current V _O < GND	-50	mA
Io	DC Output Sink Current	128	mA
I _{CC}	DC Supply Current per Supply Pin	±100	mA
I _{GND}	DC Ground Current per Ground Pin	±100	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias	+150	°C
θЈА	Thermal Resistance SOIC TSSOP QFN	125 170 N/A	°C/W
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 2000 > 200 N/A	V
I _{Latchup}	Latchup Performance Above V _{CC} and Below GND at 85°C (Note 4)	±500	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Tested to EIA/JESD22-A114-A.
- 2. Tested to EIA/JESD22-A115-A.
- 3. Tested to JESD22-C101-A.
- 4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Units
V _{CC}	Supply Voltage Operating, Data Retention Only		4.0	5.5	V
VI	Input Voltage (Note 5)		0	5.5	V
Vo	Output Voltage (HIGH or LOW State)		0	5.5	V
T _A	Operating Free–Air Temperature		-40	+85	°C
Δt/ΔV		vitch Control Input CC = 5.0 V ± 0.5 V	0	DC 5	ns/V

5. Unused control inputs may not be left open. All control inputs must be tied to a high or low logic input voltage level.

74FST3257

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	$T_A = -40$ °C to +85°C		85°C	
Symbol	Parameter	Conditions	(V)	Min	Тур*	Max	Units
V _{IK}	Clamp Diode Voltage	I _{IN} = -18 mA	4.5			-1.2	V
V _{IH}	High-Level Input Voltage		4.0 to 5.5	2.0			V
V _{IL}	Low-Level Input Voltage		4.0 to 5.5			0.8	V
I _I	Input Leakage Current	0 ≤ V _{IN} ≤ 5.5 V	5.5			±1.0	μΑ
l _{OZ}	Off–State Leakage Current	0 ≤ A, B ≤ V _{CC}	5.5			±1.0	μΑ
R _{ON}	Switch On Resistance (Note 6)	V _{IN} = 0 V, I _{IN} = 64 mA	4.5		4	7	Ω
		V _{IN} = 0 V, I _{IN} = 30 mA	4.5		4	7	
		V _{IN} = 2.4 V, I _{IN} = 15 mA	4.5		8	15	
		V _{IN} = 2.4 V, I _{IN} = 15 mA	4.0		11	20	
I _{CC}	Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND, $I_{OUT} = 0$	5.5			3	μΑ
Δl _{CC}	Increase In I _{CC} per Input	One input at 3.4 V, Other inputs at V _{CC} or GND	5.5			2.5	mA

AC ELECTRICAL CHARACTERISTICS

			$T_A = -40$ °C to +85°C $C_L = 50$ pF, RU = RD = 500 Ω		0 Ω		
			V _{CC} = 4	.5–5.5 V	V _{CC} =	4.0 V	
Symbol	Parameter	Conditions	Min	Max	Min	Max	Units
t _{PHL} ,	Prop Delay Bus to Bus (Note 7)	V _I = OPEN		0.25		0.25	ns
t _{PLH}	Prop Delay, Select to Bus A		1.0	4.7		5.2	
t _{PZH} ,	Output Enable Time, Select to Bus B	V _I = 7 V for t _{PZL}	1.0	5.2		5.7	ns
t _{PZL}	Output Enable Time, I _{OE} to Bus A, B	V _I = OPEN for t _{PZH}	1.0	5.1		5.6	
t _{PHZ} ,	Output Disable Time, Select to Bus B	$V_I = 7 \text{ V for } t_{PLZ}$	1.0	5.2		5.5	ns
t _{PLZ}	Output Disable Time, I _{OE} to Bus A, B	$V_I = OPEN$ for t_{PHZ}	1.0	5.5		5.5	

^{7.} This parameter is guaranteed by design but is not tested. The bus switch contributes no propagation delay other than the RC delay of the typical On resistance of the switch and the 50 pF load capacitance, when driven by an ideal voltage source (zero output impedance).

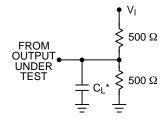
CAPACITANCE (Note 8)

Symbol	Parameter	Conditions	Тур	Max	Units
C _{IN}	Control Pin Input Capacitance	V _{CC} = 5.0 V	3		pF
C _{I/O}	A Port Input/Output Capacitance	V_{CC} , $\overline{OE} = 5.0 \text{ V}$	7		pF
C _{I/O}	B Port Input/Output Capacitance	V_{CC} , $\overline{OE} = 5.0 \text{ V}$	5		pF

^{8.} $T_A = +25^{\circ}C$, f = 1 MHz, Capacitance is characterized but not tested.

^{*}Typical values are at V_{CC} = 5.0 V and T_A = 25°C.
6. Measured by the voltage drop between A and B pins at the indicated current through the switch. On resistance is determined by the lower of the voltages on the two (A or B) pins.

AC Loading and Waveforms



NOTES:

- 1. Input driven by 50 Ω source terminated in 50 Ω .
- 2. CL includes load and stray capacitance.

Figure 4. AC Test Circuit

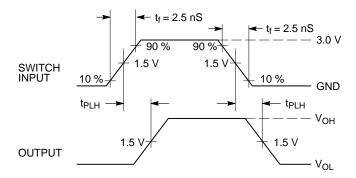


Figure 5. Propagation Delays

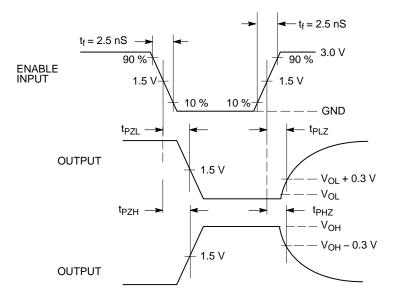
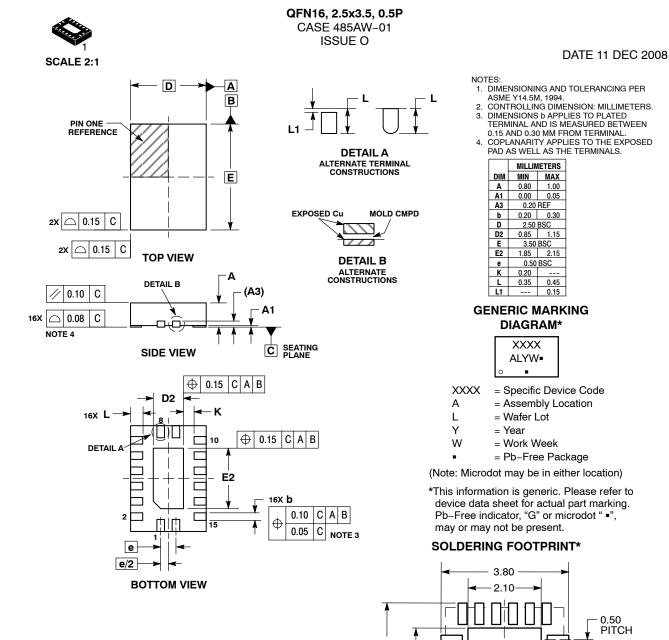


Figure 6. Enable/Disable Delays

 $^{{}^{*}}C_{L} = 50 pF$



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

16X

0.30

DIMENSIONS: MILLIMETERS

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2.80

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16X 0.60

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PACKAGE

MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050	BSC
7	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

16. COLLECTOR 16. CATHODE 16. COLLECTOR, #4 16. EMITTER, #1 STYLE 5: STYLE 6: STYLE 7: PIN 1. DRAIN, DYE #1 PIN 1. CATHODE 2. COMMON DRAIN (OUTPUT) 3. DRAIN, #1 2. CATHODE 2. COMMON DRAIN (OUTPUT) 4. DRAIN, #2 3. CATHODE 3. COMMON DRAIN (OUTPUT) 5. DRAIN, #3 5. CATHODE 4. GATE P-CH 7. DRAIN, #3 6. CATHODE 5. COMMON DRAIN (OUTPUT) 8. DRAIN, #4 7. CATHODE 7. COMMON DRAIN (OUTPUT) 8. DRAIN, #4 8. CATHODE 8. SOURCE P-CH 9. GATE, #4 9. ANODE 9. SOURCE P-CH 10. SOURCE, #4 10. ANODE 10. COMMON DRAIN (OUTPUT) 11. GATE, #3 11. ANODE 11. COMMON DRAIN (OUTPUT) 12. SOURCE, #3 12. ANODE 13. GATE N-CH 14. SOURCE, #2 14. ANODE 14. COMMON DRAIN (OUTPUT) 15. GATE, #1 15. ANODE 16. SOURCE N-CH 16. SOURCE, #1 16. ANODE 16. SOURCE N-CH	STYLE 1: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE	2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	CATHODE CATHODE ANODE NO CONNECTION CATHODE CATHODE NO CONNECTION	STYLE 3: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #3 BASE, #3 EMITTER, #3 COLLECTOR, #3 COLLECTOR, #4	STYLE 4: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COLLECTOR, DYE #1 COLLECTOR, #1 COLLECTOR, #2 COLLECTOR, #3 COLLECTOR, #3 COLLECTOR, #4 COLLECTOR, #4 EMITTER, #4 BASE, #4 EMITTER, #4 BASE, #3 EMITTER, #3 BASE, #2 EMITTER, #2 BASE, #1		FOOTPRINT
STYLE 5:										
	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 GATE, #1	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT GATE P-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT GATE N-CH COMMON DRAIN (OUTPUT GATE N-CH COMMON DRAIN (OUTPUT COMMON DRAIN COMMON DRAIN (OUTPUT COMMON DRAIN COMMON DRAIN COMMON DRAIN (OUTPUT COMMON DRAIN COMMON DRAIN COMMON DRAIN COMMON DRAIN COMMON DRAI	n n n n n n	16X 0.58	<u> </u>	16X 1.12

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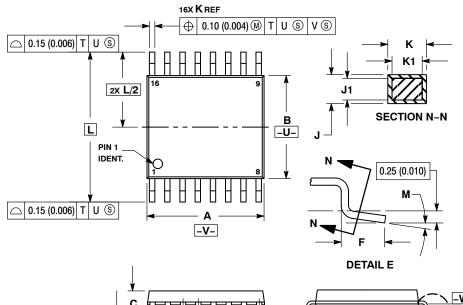
-T- SEATING PLANE





TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006



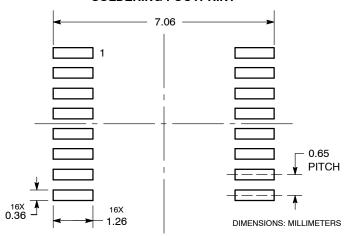
NOTES

- JIES:
 DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH. PROTRUSIONS OR GATE BURRS.
 MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Ы	6.40 BSC		0.252 BSC	
М	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT

G



GENERIC MARKING DIAGRAM*

168888888 XXXX XXXX **ALYW** 188888888

XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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